



### 60V +175°C N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

# **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub>	I <sub>D</sub> Tc = +25°C
60V	1.6mΩ @ V <sub>GS</sub> = 10V	215A

## **Features**

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- High Conversion Efficiency
- Low R<sub>DS(ON)</sub> Minimizes On State Losses
- Low Input Capacitance
- Fast Switching Speed
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMTH61M8SPSQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

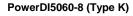
# **Description and Applications**

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP, and is ideal for use in:

- Engine Management Systems
- Body Control Electronics
- DC-DC Converters

### **Mechanical Data**

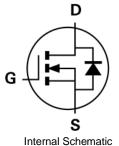
- Case: PowerDI<sup>®</sup>5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
   Solderable per MIL-STD-202, Method 208 63
- Weight: 0.097 grams (Approximate)

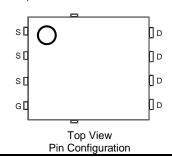






op View Bottom View





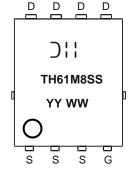
### **Ordering Information** (Note 4)

Part Number	Case	Packaging
DMTH61M8SPSQ-13	PowerDI5060-8 (Type K)	2,500 / Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

# **Marking Information**



#### PowerDI5060-8 (Type K)

);; = Manufacturer's Marking
TH61M8SS = Product Type Marking Code
YYWW = Date Code Marking
YY = Year (ex: 20 = 2020)
WW = Week (01 to 53)

PowerDI is a registered trademark of Diodes Incorporated.



## **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage		$V_{DSS}$	60	V
Gate-Source Voltage		Vgss	±20	V
Continuous Drain Current, V <sub>GS</sub> = 10V (Note 6)	T <sub>C</sub> = +25°C T <sub>C</sub> = +100°C	l <sub>D</sub>	215 150	Α
Maximum Continuous Body Diode Forward Current (Note 6)	Is	215	А	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I <sub>DM</sub>	860	А
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)		Ism	860	Α
Avalanche Current, L = 1mH		las	35.8	А
Avalanche Energy, L = 1mH		Eas	640.8	mJ

# Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T <sub>A</sub> = +25°C	PD	3.2	W
Thermal Resistance, Junction to Ambient (Note 5)		R <sub>θ</sub> JA	47	°C/W
Total Power Dissipation (Note 6)	$T_C = +25^{\circ}C$	$P_{D}$	167	W
Thermal Resistance, Junction to Case (Note 6)		$R_{ heta JC}$	0.9	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +175	°C

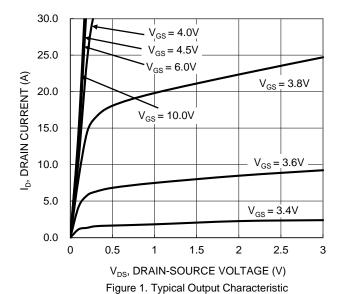
# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BVDSS	60	-	_	V	$V_{GS} = 0V, I_{D} = 250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>		I	1	μΑ	$V_{DS} = 48V$ , $V_{GS} = 0V$	
Gate-Source Leakage	Igss		-	±100	nA	$V_{GS} = \pm 20V$ , $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	2	1	4	V	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$	
Static Drain-Source On-Resistance	RDS(ON)	I	1.1	1.6	mΩ	VGS = 10V, ID = 30A	
Diode Forward Voltage	$V_{SD}$	l	0.7	1.2	V	$V_{GS} = 0V, I_{S} = 20A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss		8306	_		V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V, f = 1MHz	
Output Capacitance	Coss	l	2735		pF		
Reverse Transfer Capacitance	Crss		184	_			
Gate Resistance	$R_g$	_	3.0	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge	Qg	_	130.6	_			
Gate-Source Charge	Qgs	_	30.4	_	nC	V <sub>DS</sub> = 30V, I <sub>D</sub> = 30A, V <sub>GS</sub> = 10V	
Gate-Drain Charge	Qgd	_	28.1	_			
Turn-On Delay Time	td(ON)	_	11.3	_		$V_{DD} = 30V, V_{GS} = 10V,$ $I_{D} = 30A, R_{g} = 3\Omega$	
Turn-On Rise Time	t <sub>R</sub>	_	28.5	_	no		
Turn-Off Delay Time	tD(OFF)	I	86.2	_	ns		
Turn-Off Fall Time	t <sub>F</sub>	1	47.6	_			
Body Diode Reverse Recovery Time	trr	_	70.4	_	ns	I <sub>F</sub> = 30A, di/dt = 100A/µs	
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>		127		nC	- 1 = 30A, αι/αι = 100A/μs	

 Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
 Thermal resistance from junction to soldering point (on the exposed drain pad).
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing. Notes:

DMTH61M8SPSQ Document number: DS40996 Rev. 7 - 2





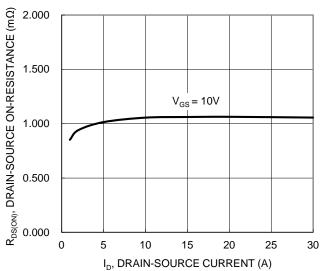


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

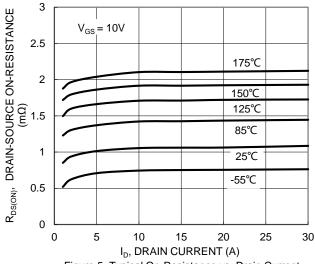


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

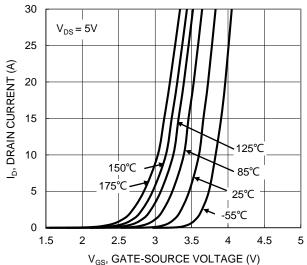


Figure 2. Typical Transfer Characteristic

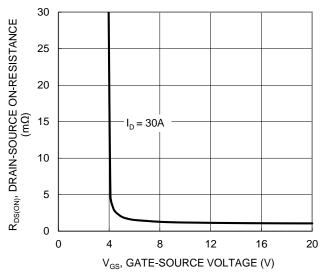


Figure 4. Typical Transfer Characteristic

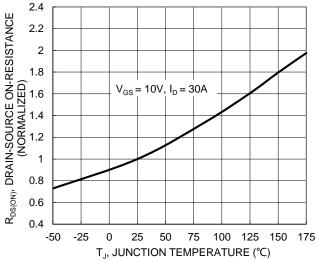


Figure 6. On-Resistance Variation with Temperature



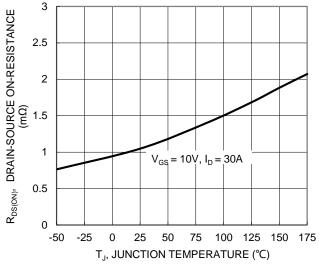


Figure 7. On-Resistance Variation with Temperature

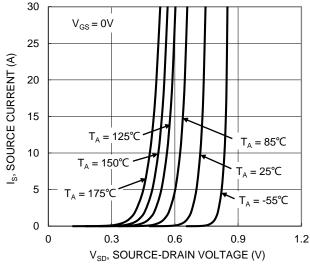


Figure 9. Diode Forward Voltage vs. Current

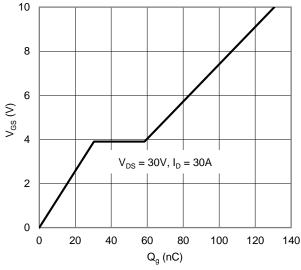


Figure 11. Gate Charge

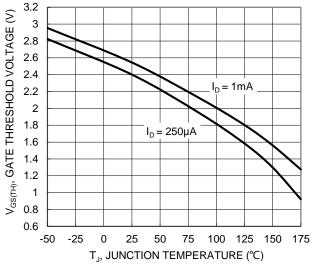
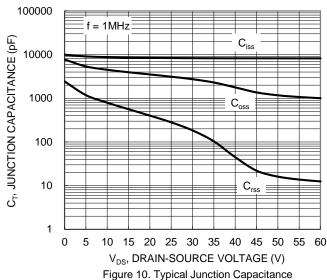


Figure 8. Gate Threshold Variation vs. Junction Temperature



1000 R<sub>DS(ON)</sub> 100 ID, DRAIN CURRENT (A)  $P_W = 10 \mu s$ 10 T<sub>C</sub> = 25°C  $P_W = 100 ms$ Single Pulse DUT on Infinite Heatsink  $V_{GS} = 10V$ 0.1 0.1 100 V<sub>DS</sub>, DRAIN-SOURCE VOLTAGE (V) Figure 12. SOA, Safe Operation Area



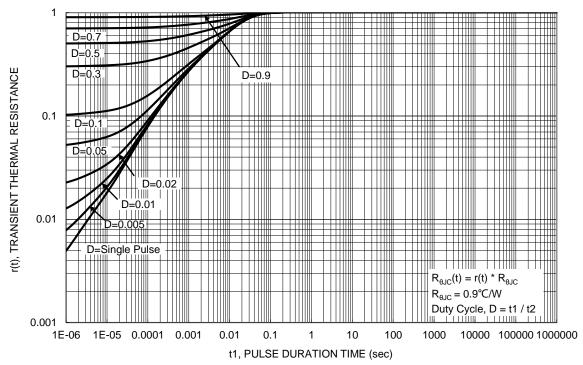


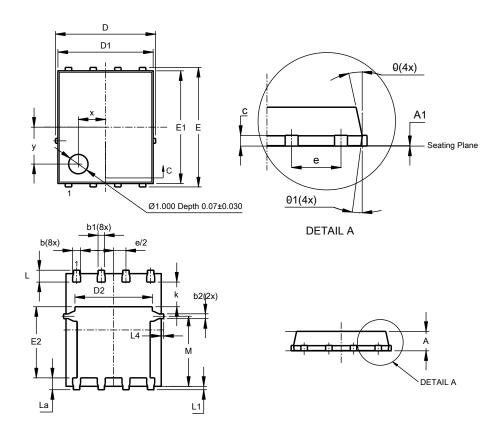
Figure 13. Transient Thermal Resistance



# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### PowerDI5060-8 (Type K)

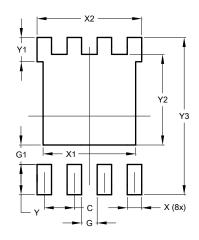


PowerDI5060-8 (Type K)						
Dim	Min	Max	Тур			
Α	0.90	1.10	1.00			
A1	0	0.05	0.02			
b	0.33	0.51	0.41			
b1	0.300	0.366	0.333			
b2	0.20	0.35	0.25			
С	0.23	0.33	0.277			
D	5	.15 BS0	)			
D1	4.85	4.95	4.90			
D2	-	-	3.98			
Е	6	.15 BS0	)			
E1	5.75	5.85	5.80			
E2	3.56	3.725	3.66			
е	1	.27BSC	;			
k	-	-	1.27			
L	0.51	0.71	0.61			
La	0.51	0.675	0.61			
L1	0.05	0.20	0.175			
L4	-	-	0.125			
М	3.50	3.71	3.605			
X	-	-	1.400			
У	-	-	1.900			
θ	10°	12°	11°			
θ1	6°	8°	7°			
All Dimensions in mm						

# Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI5060-8 (Type K)



Dimensions	Value (in mm)		
С	1.270		
G	0.660		
G1	0.820		
X	0.610		
X1	3.910		
X2	4.420		
Y	1.270		
Y1	1.020		
Y2	3.810		
Y3	6.610		



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